

## SWITCHING

## N-CHANNEL POWER MOS FET

### DESCRIPTION

The 2SK3575 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

### FEATURES

- 4.5V drive available
- Low on-state resistance  
 $R_{DS(on)1} = 4.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 42 \text{ A)}$
- Low gate charge  
 $Q_G = 70 \text{ nC TYP. (} V_{DD} = 24 \text{ V, } V_{GS} = 10 \text{ V, } I_D = 83 \text{ A)}$
- Avalanche capability ratings
- Surface mount device available

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

|                                                      |                |                        |                  |
|------------------------------------------------------|----------------|------------------------|------------------|
| Drain to Source Voltage ( $V_{GS} = 0 \text{ V}$ )   | $V_{DSS}$      | 30                     | V                |
| Gate to Source Voltage ( $V_{DS} = 0 \text{ V}$ )    | $V_{GSS}$      | $\pm 20$               | V                |
| Drain Current (DC) ( $T_C = 25^\circ\text{C}$ )      | $I_{D(DC)}$    | $\pm 83$               | A                |
| Drain Current (pulse) <b>Note1</b>                   | $I_{D(pulse)}$ | $\pm 332$              | A                |
| Total Power Dissipation ( $T_A = 25^\circ\text{C}$ ) | $P_{T1}$       | 1.5                    | W                |
| Total Power Dissipation ( $T_C = 25^\circ\text{C}$ ) | $P_{T2}$       | 105                    | W                |
| Channel Temperature                                  | $T_{ch}$       | 150                    | $^\circ\text{C}$ |
| Storage Temperature                                  | $T_{stg}$      | $-55 \text{ to } +150$ | $^\circ\text{C}$ |
| Single Avalanche Current <b>Note2</b>                | $I_{AS}$       | 57                     | A                |
| Single Avalanche Energy <b>Note2</b>                 | $E_{AS}$       | 325                    | mJ               |

**Notes 1.**  $PW \leq 10 \mu\text{s}$ , Duty Cycle  $\leq 1\%$

**2.** Starting  $T_{ch} = 25^\circ\text{C}$ ,  $V_{DD} = 15 \text{ V}$ ,  $R_G = 25 \Omega$ ,  $V_{GS} = 20 \rightarrow 0 \text{ V}$

### ★ ORDERING INFORMATION

| PART NUMBER | PACKAGE                   |
|-------------|---------------------------|
| 2SK3575     | TO-220AB                  |
| 2SK3575-S   | TO-262                    |
| 2SK3575-ZK  | TO-263                    |
| 2SK3575-Z   | TO-220SMD <sup>Note</sup> |

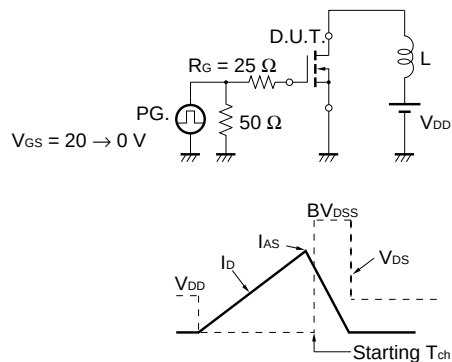
**Note** TO-220SMD package is produced only in Japan.

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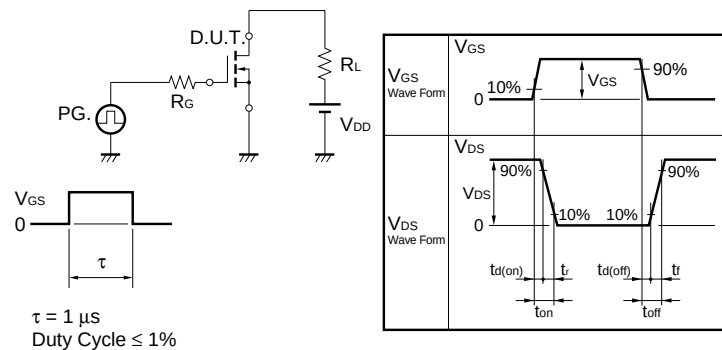
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)**

| CHARACTERISTICS                     | SYMBOL               | TEST CONDITIONS                                | MIN. | TYP. | MAX. | UNIT |
|-------------------------------------|----------------------|------------------------------------------------|------|------|------|------|
| Zero Gate Voltage Drain Current     | I <sub>DSS</sub>     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V  |      |      | 10   | μA   |
| Gate Leakage Current                | I <sub>GSS</sub>     | V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V |      |      | ±100 | nA   |
| Gate Cut-off Voltage                | V <sub>GS(off)</sub> | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA  | 1.5  |      | 2.5  | V    |
| Forward Transfer Admittance         | y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 42 A  | 27   |      |      | S    |
| Drain to Source On-state Resistance | R <sub>DS(on)1</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 42 A  |      | 3.3  | 4.5  | mΩ   |
|                                     | R <sub>DS(on)2</sub> | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 42 A |      | 4.3  | 6.4  | mΩ   |
| Input Capacitance                   | C <sub>iss</sub>     | V <sub>DS</sub> = 10 V                         |      | 3700 |      | pF   |
| Output Capacitance                  | C <sub>oss</sub>     | V <sub>GS</sub> = 0 V                          |      | 1430 |      | pF   |
| Reverse Transfer Capacitance        | C <sub>rss</sub>     | f = 1 MHz                                      |      | 500  |      | pF   |
| Turn-on Delay Time                  | t <sub>d(on)</sub>   | V <sub>DD</sub> = 15 V, I <sub>D</sub> = 42 A  |      | 26   |      | ns   |
| Rise Time                           | t <sub>r</sub>       | V <sub>GS</sub> = 10 V                         |      | 27   |      | ns   |
| Turn-off Delay Time                 | t <sub>d(off)</sub>  | R <sub>G</sub> = 10 Ω                          |      | 110  |      | ns   |
| Fall Time                           | t <sub>f</sub>       |                                                |      | 40   |      | ns   |
| Total Gate Charge                   | Q <sub>G</sub>       | V <sub>DD</sub> = 24 V                         |      | 70   |      | nC   |
| Gate to Source Charge               | Q <sub>GS</sub>      | V <sub>GS</sub> = 10 V                         |      | 12   |      | nC   |
| Gate to Drain Charge                | Q <sub>GD</sub>      | I <sub>D</sub> = 83 A                          |      | 20   |      | nC   |
| Body Diode Forward Voltage          | V <sub>F(S-D)</sub>  | I <sub>F</sub> = 83 A, V <sub>GS</sub> = 0 V   |      | 1.0  |      | V    |
| Reverse Recovery Time               | t <sub>rr</sub>      | I <sub>F</sub> = 83 A, V <sub>GS</sub> = 0 V   |      | 61   |      | ns   |
| Reverse Recovery Charge             | Q <sub>rr</sub>      | di/dt = 100 A/μs                               |      | 94   |      | nC   |

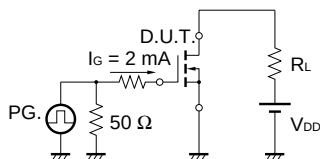
★ **TEST CIRCUIT 1 AVALANCHE CAPABILITY**



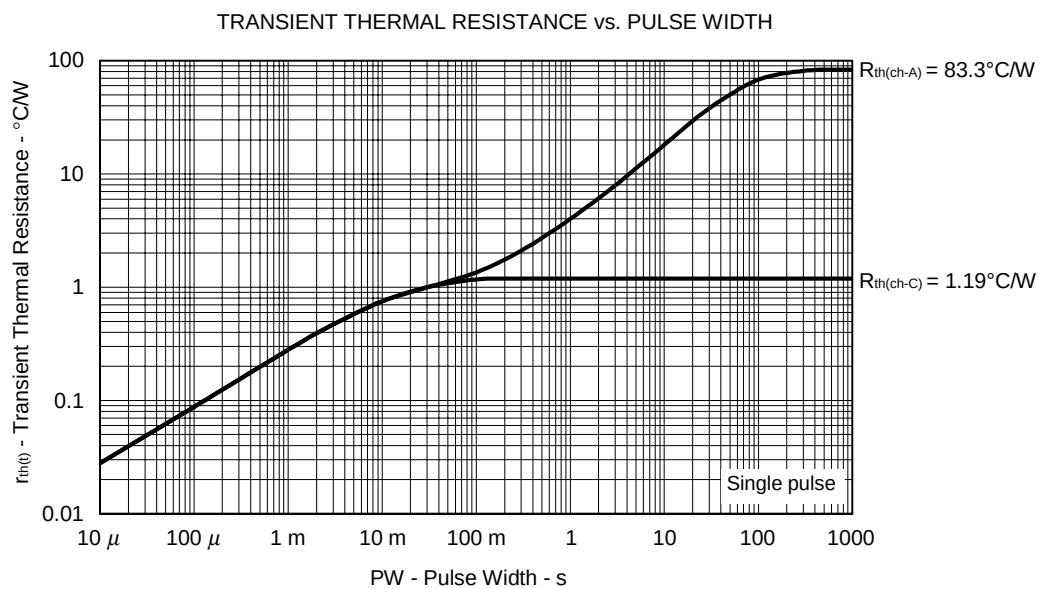
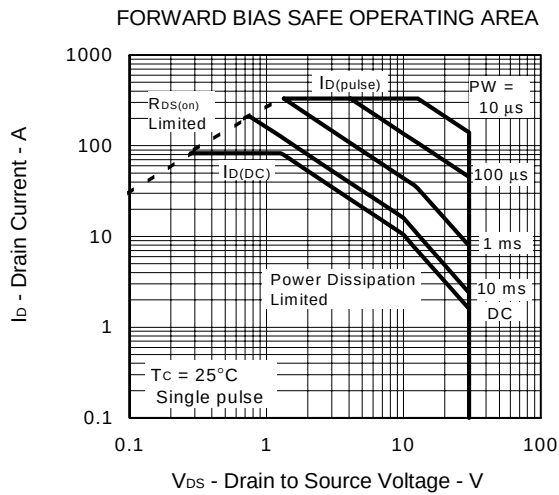
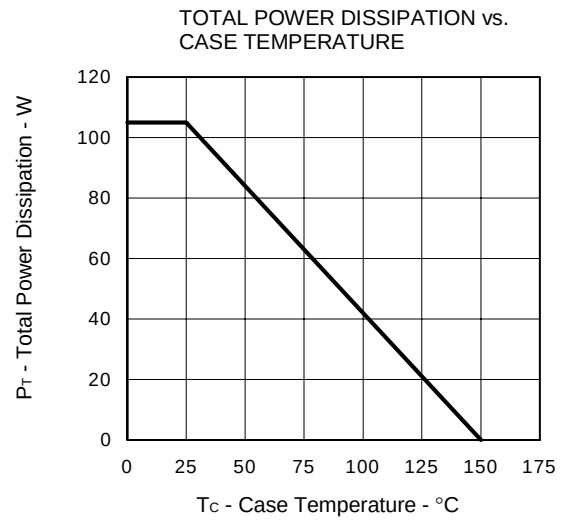
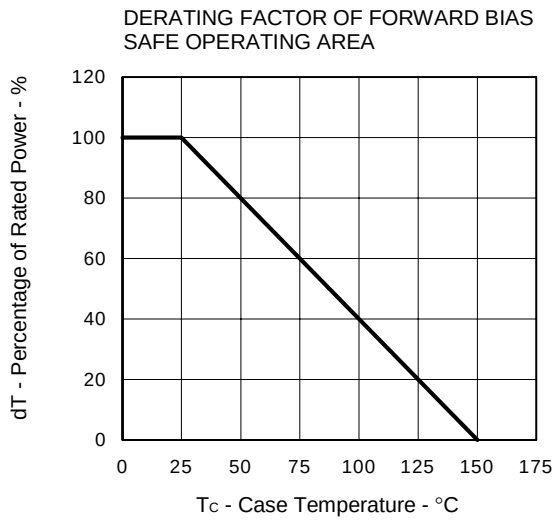
**TEST CIRCUIT 2 SWITCHING TIME**



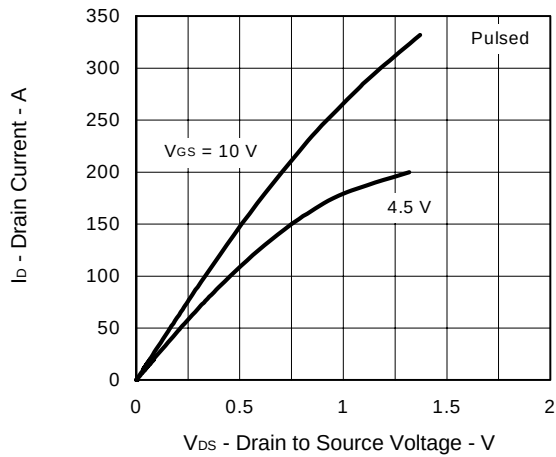
**TEST CIRCUIT 3 GATE CHARGE**



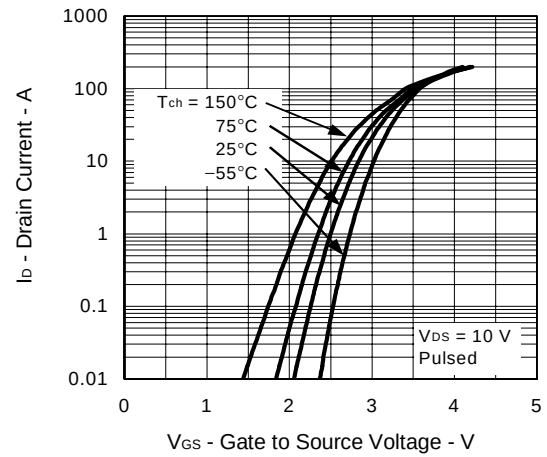
TYPICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ )



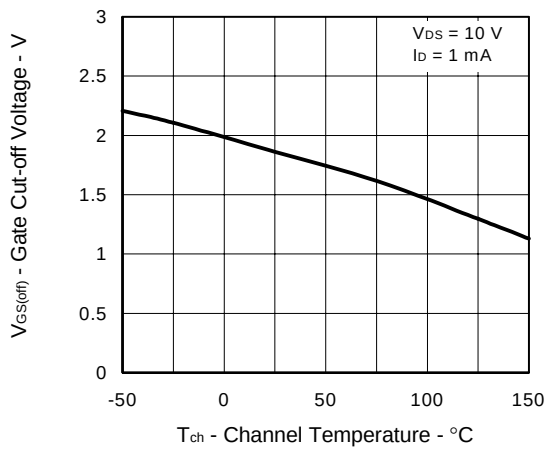
DRAIN CURRENT vs.  
DRAIN TO SOURCE VOLTAGE



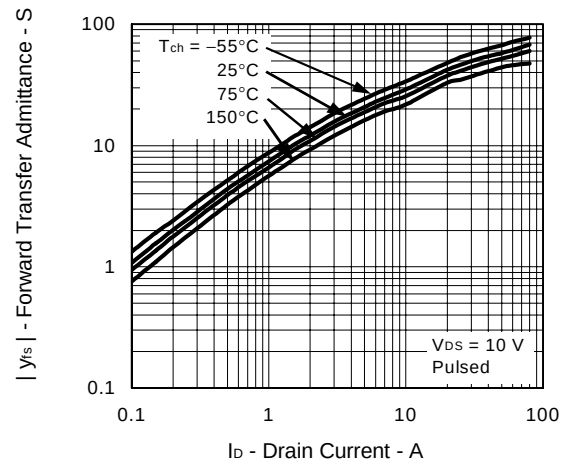
FORWARD TRANSFER CHARACTERISTICS



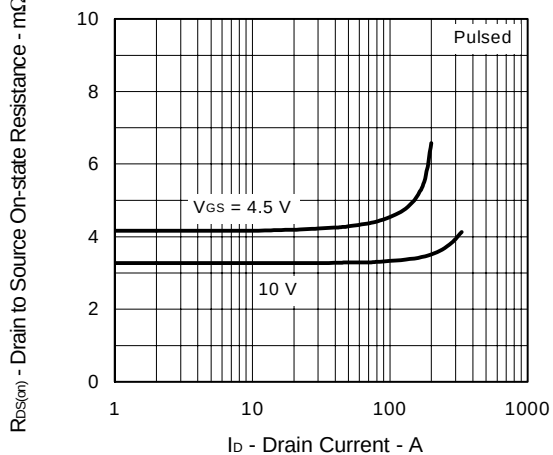
GATE CUT-OFF VOLTAGE vs.  
CHANNEL TEMPERATURE



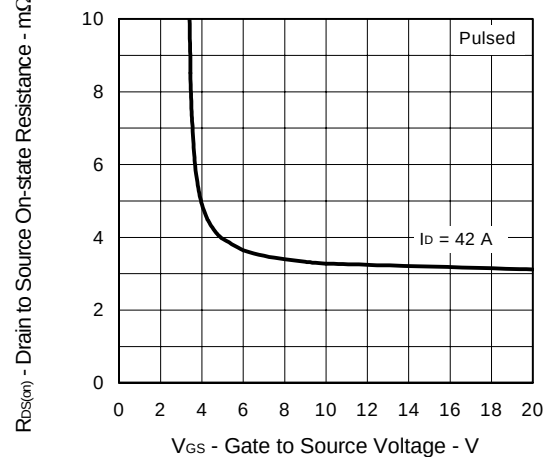
FORWARD TRANSFER ADMITTANCE vs.  
DRAIN CURRENT



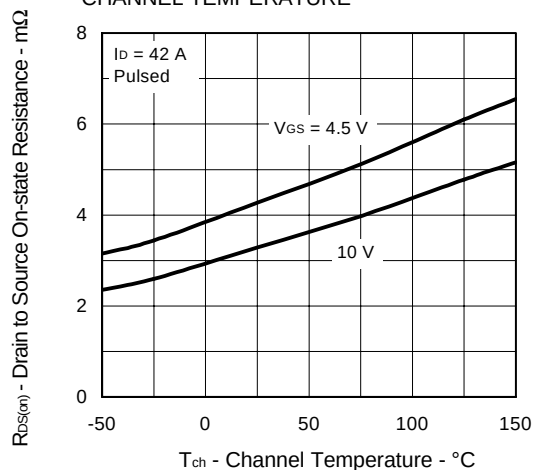
DRAIN TO SOURCE ON-STATE RESISTANCE vs.  
DRAIN CURRENT



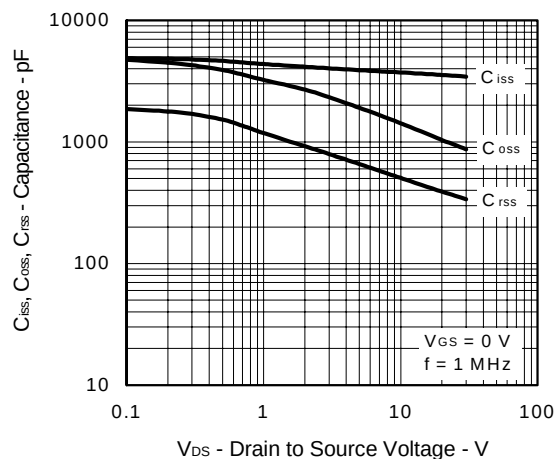
DRAIN TO SOURCE ON-STATE RESISTANCE vs.  
GATE TO SOURCE VOLTAGE



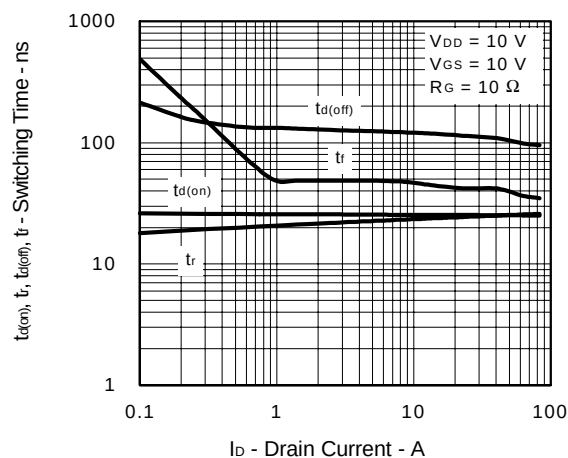
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



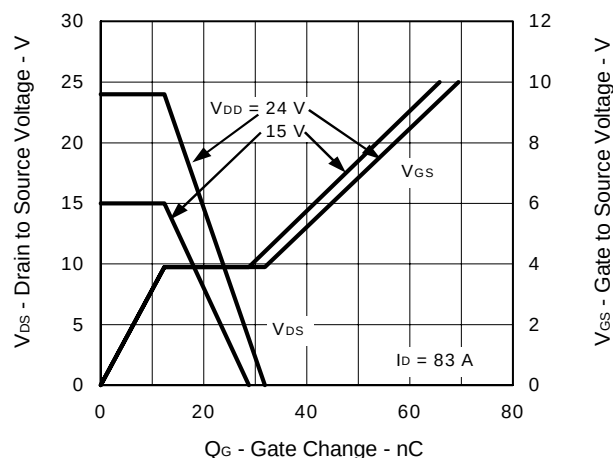
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



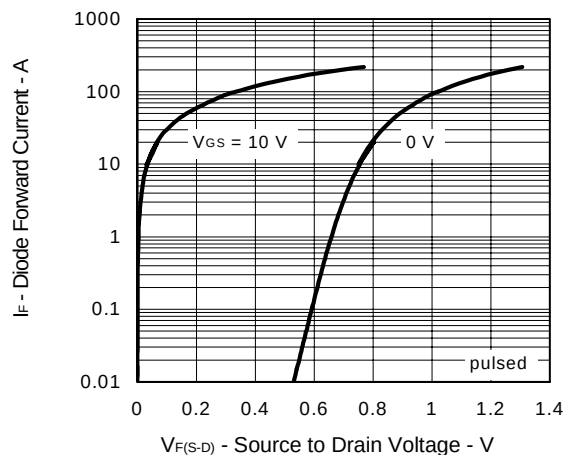
SWITCHING CHARACTERISTICS



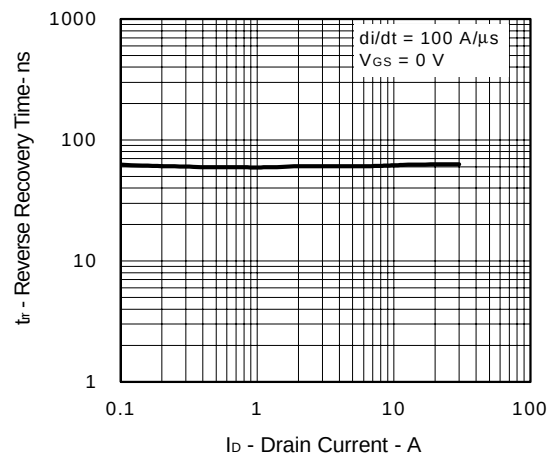
DYNAMIC INPUT/OUTPUT CHARACTERISTICS

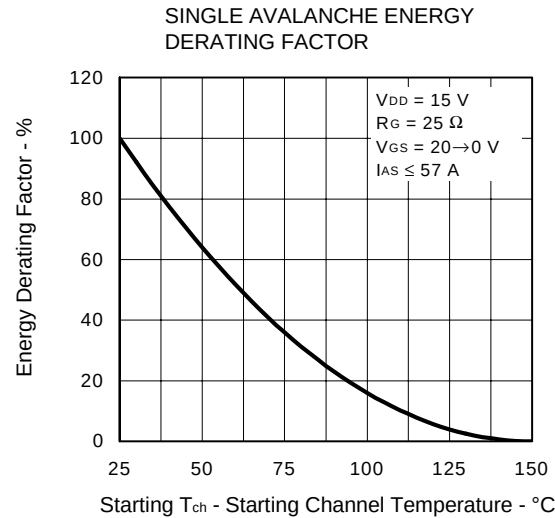
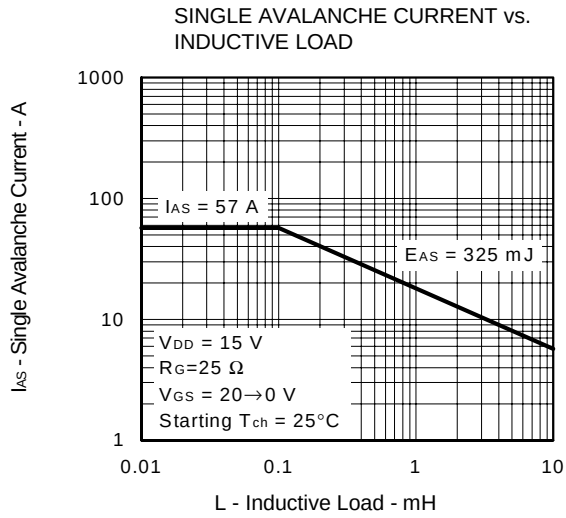


SOURCE TO DRAIN DIODE FORWARD VOLTAGE



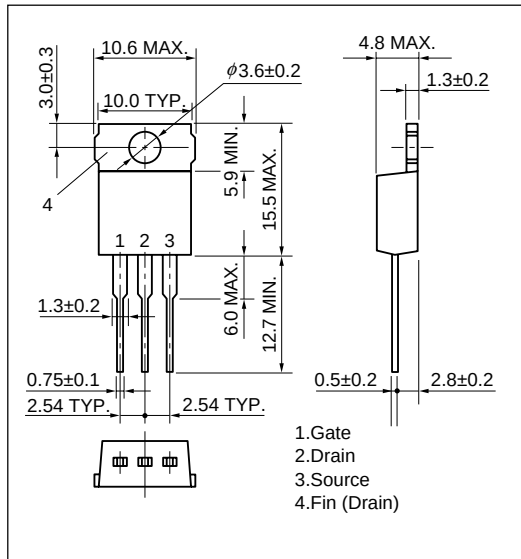
REVERSE RECOVERY TIME vs. DRAIN CURRENT



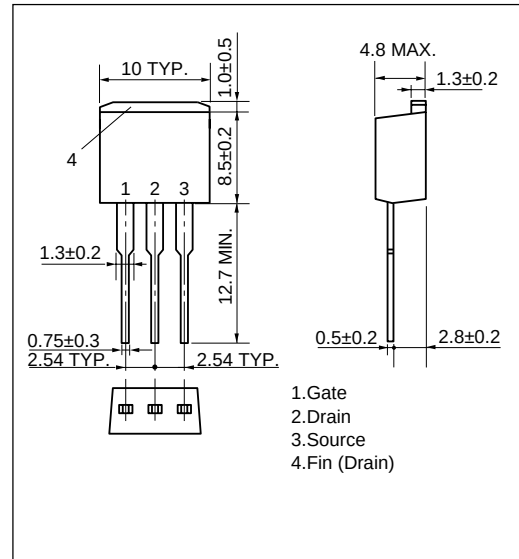


★ PACKAGE DRAWINGS (Unit: mm)

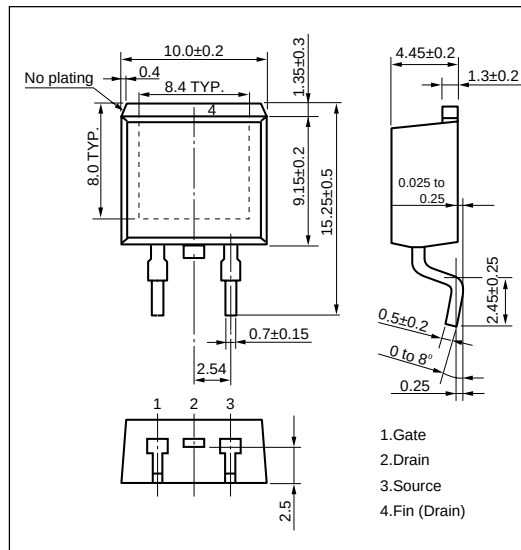
1) TO-220AB(MP-25)



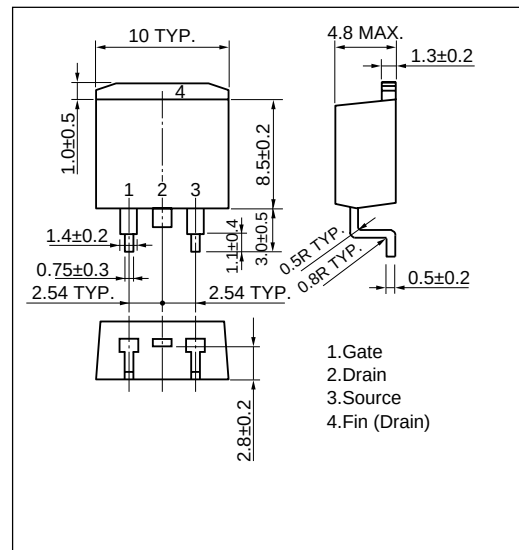
2) TO-262(MP-25 Fin Cut)



3) TO-263(MP-25ZK)

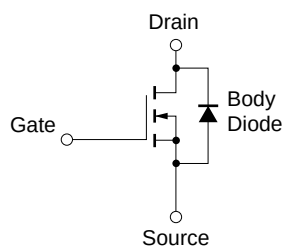


4) TO-220SMD(MP-25Z)<sup>Note</sup>



**Note** This package is produced only in Japan.

EQUIVALENT CIRCUIT



**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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